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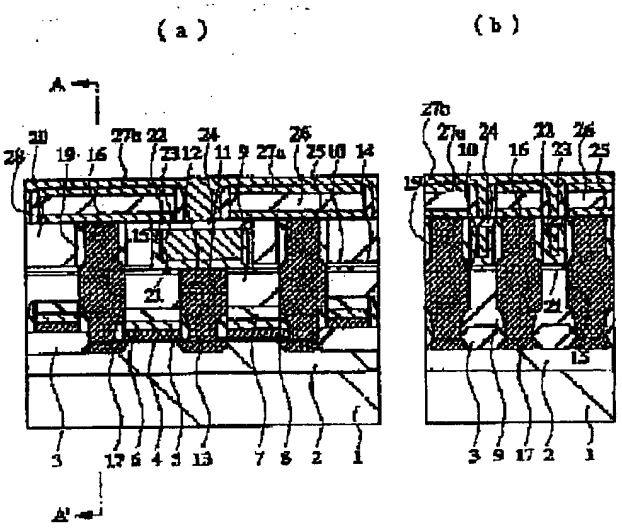
TITLE : SEMICONDUCTOR INTEGRATED CIRCUIT DEVICE AND ITS MANUFACTURING METHOD




ABSTRACT : PROBLEM TO BE SOLVED: To make a memory cell finer and also to realize fast operation of a DRAM for a DRAM, provided with a memory cell of COB(capacitor over bit line) structure.

SOLUTION: For a pillar-like polycrystal line silicon film 1, which connects an accumulating electrode 25 of information accumulation capacitance element and an n-type semiconductor region 17 of MISFET(metal insulator semiconductor filed effect transistor) for memory selection, a bit-line compressing a tungsten film 23 and an adhesive layer 22 is formed by self-matching. The bit-line and a part of a sidewall of the bit-line are covered with a silicon oxide film 24 of low dielectric constant and a silicon oxide film 20, respectively.